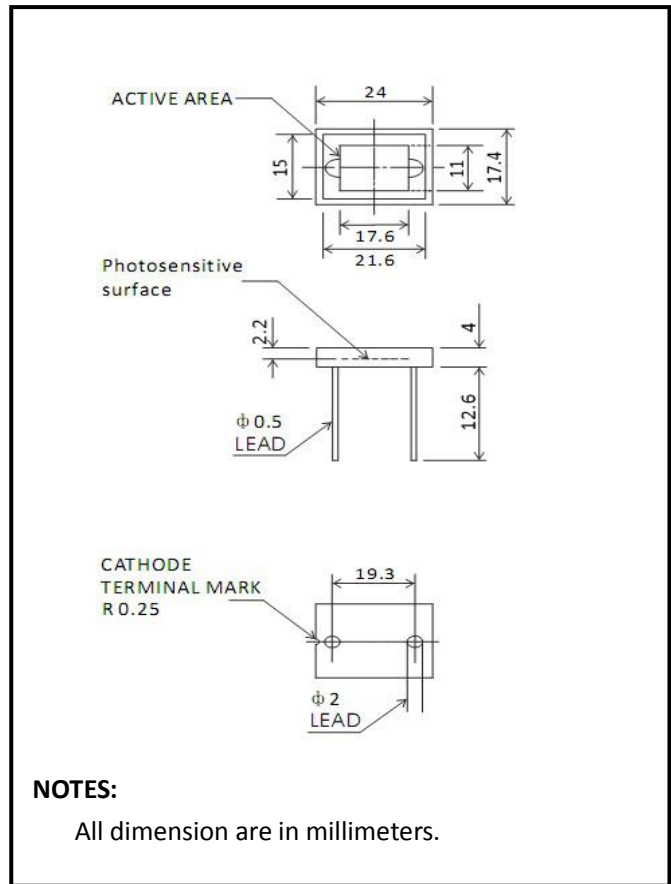


## Large Active Area Silicon Photodiode OSD150-IC



### Description

The OSD150-IC is high-output, high sensitivity silicon Photodiode mounted in ceramic with glass package, Permits wide angular response.

### Features

- \* High sensitivity, high speed response
- \* Wide angular response
- \* High reliability in demanding environments
- \* Operating temperature is from -40 to +80°C
- \* Storage temperature is from -40 to +100°C
- \* soldering temperature is 260°C @Max.5 seconds at the position of 2mm from the PIN legs.

### General Ratings

- \* Type Silicon Photodiode
- \* High linearity
- \* Low cost
- \* Low dark current

### Applications

- \* Analytical instruments
- \* Precision photometry
- \* Fluorescence detector
- \* IR/ Laser light Monitoring
- \* Optical measurement equipment
- \* Medical equipment
- \* Spectrum photometry/CT scan

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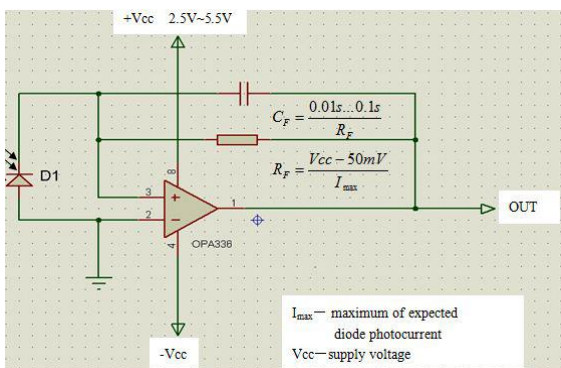
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[Http://www.otronsensor.com](http://www.otronsensor.com)

## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Short circuit Current	I <sub>SC</sub>	Ev=100lx fc=2856k*		134		μA
Isc Temperature Coefficient	TC I <sub>sc</sub>	2856k		1.2		%/°C
Open Circuit Voltage	V <sub>oc</sub>	Ev=100lx fc=2856k*		347		mV
Voc Temperature Coefficient	TC Voc	2856k		-2.2		mV/°C
Dark current	I <sub>D</sub>	VR=10mV		1		nA
		VR=10V		5		
Rise time	t <sub>R</sub>	V <sub>R</sub> =0V; λ=635nm; R <sub>L</sub> =50Ω, f=1KHz		580		ns
		V <sub>R</sub> =0V; λ=635nm; R <sub>L</sub> =50Ω, f=1KHz		480		
Temp coefficient of I <sub>D</sub>	T <sub>CID</sub>			0.18		times/°C
Reverse breakdown voltage	V <sub>(BR)R</sub>	I <sub>R</sub> =100μA Ev=0lx	50			V
Junction Capacitance	C <sub>J</sub>	V <sub>R</sub> =0V f=1MHz		128		pF
		V <sub>R</sub> =10V f=1MHz		25		
Photo sensitivity	S <sub>R</sub>	650nm		0.37		A/W
		940nm		0.66		
Spectral Application Range	λ <sub>range</sub>		400		1100	nm
Spectral Response-Peak	λ <sub>p</sub>			940		nm
Shunt resistance	R <sub>sh</sub>	VR=10mV		0.01		GΩ
Rsh Temperature Coefficient	TC R <sub>sh</sub>			0.18		%/°C
Angular Resp 50% Resp Pt	θ <sub>1/2</sub>			±60		Degrees
Noise Equivalent Power	NEP	V <sub>R</sub> =10V λ=940nm		6.25×10 <sup>-14</sup>		W/Hz <sup>1/2</sup>
Specific Detectivity	D*	V <sub>R</sub> =10V λ=940nm		1.6×10 <sup>13</sup>		cm(Hz/W) <sup>1/2</sup>

\* Ev: Illuminance by CIE standard light source A (tungsten lamp)

## Typical application circuit



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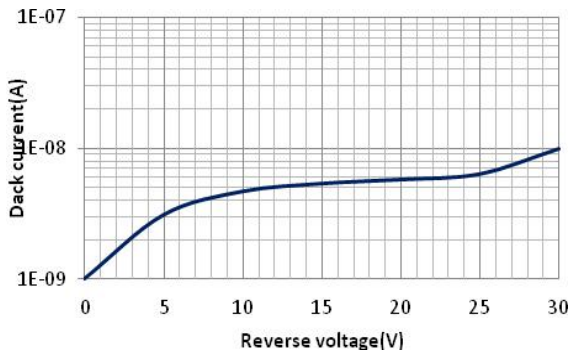
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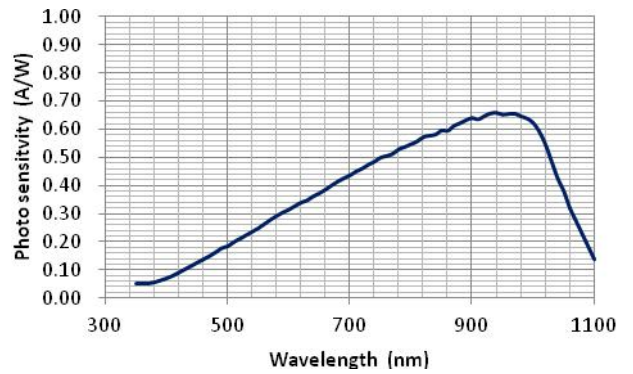


# OSD150-IC

## ■ Dark current vs. reverse voltage

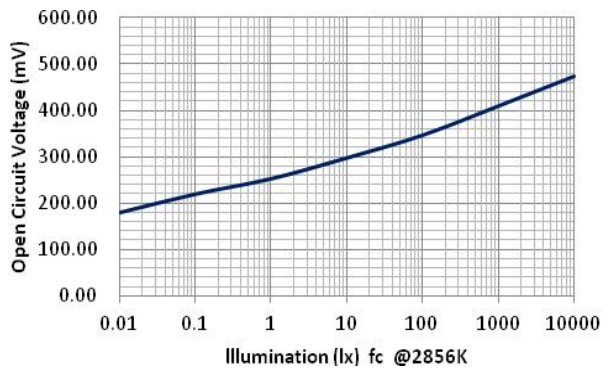


## ■ Spectral response



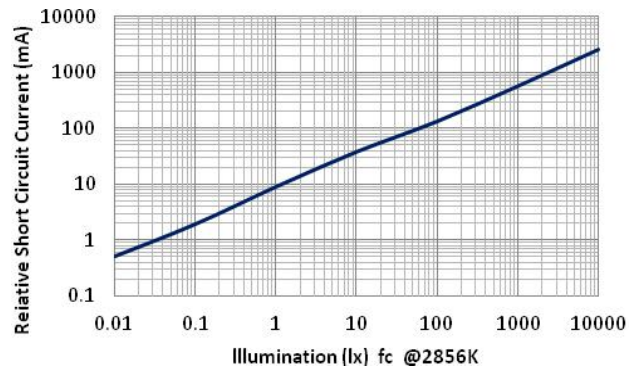
## ■ Open circuit Voltage

Vs. Illumination



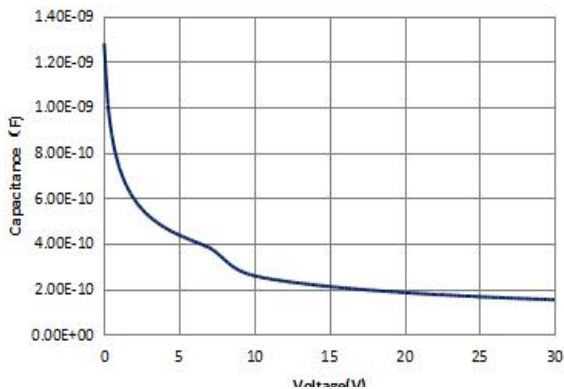
## ■ Relative Short Circuit

Current vs. Illumination

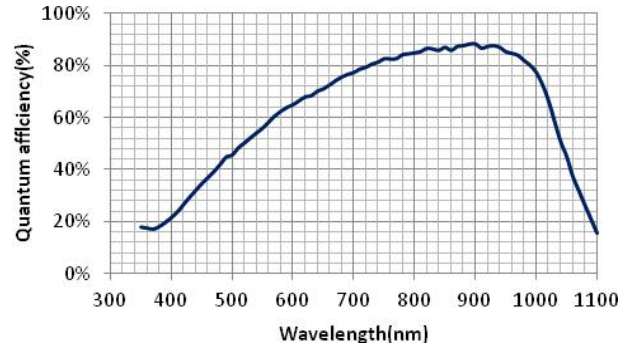


## ■ Relative Junction Capacitance

VS. Voltage



## ■ Quantum efficiency



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